Product data sheet

Product profile

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features

- Extremely fast switching
- Reduces switching loss in associated **MOSFET**
- Low thermal resistance
- Low reverse recovery current

1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies
- Half-bridge lighting ballasts
- Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- $V_F = 1.54 \text{ V (typ)}$

- $I_{F(AV)} \le 20 \text{ A}$
- $t_{rr} = 19 \text{ ns (typ)}$

Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k — a 001aaa020
mb	mounting base; cathode	1 2	
		SOD59 (2-lead TO-220)	AC)



3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BYC20-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_{mb} \le 100$ °C	-	500	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 93 $^{\circ}C$	-	20	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 93 °C; t_p = 25 $\mu s;$	-	40	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	250	А
		t = 8.3 ms; sinusoidal waveform	-	274	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; see Figure 1	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

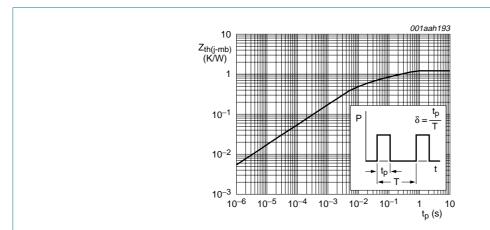


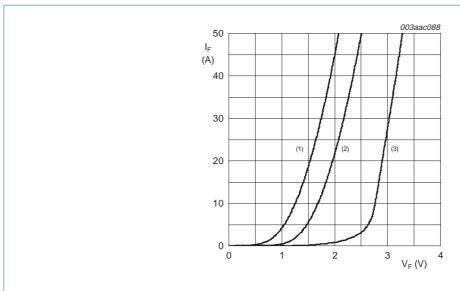
Fig 1. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 5. Characteristics

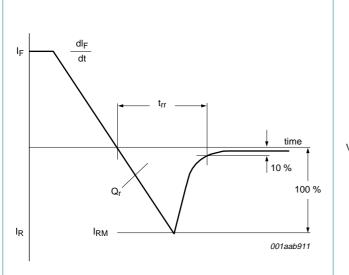
 $T_j = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 20 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	1.54	1.97	V
		$I_F = 40 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	1.95	2.34	V
		I _F = 20 A; see Figure 2	-	1.89	2.9	V
I _R	reverse current	V _R = 600 V	-	16	200	μΑ
		$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.6	3.0	mA
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	I_F = 1 A to V_R = 30 V; dI_F/dt = 50 A/ μ s; see Figure 3	-	35	55	ns
		$I_F = 20 \text{ A to } V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A/}\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{\text{I}}$				
		T _j = 25 °C	-	19	-	ns
		T _j = 100 °C	-	32	40	ns
I _{RM}	peak reverse recovery current	I_F = 20 A to V_R = 400 V; T_j = 125 °C; see Figure 3				
		$dI_F/dt = 50 A/\mu s$	-	3.0	7.5	Α
		$dI_F/dt = 500 A/\mu s$	-	9.5	12	Α
V_{FR}	forward recovery voltage	$I_F = 20 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 4	-	8	11	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage



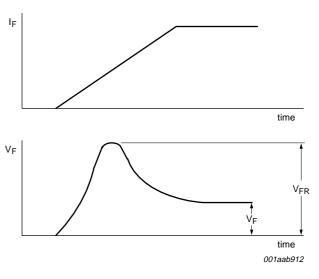


Fig 3. Reverse recovery definitions

Fig 4. Forward recovery definitions

6 of 10

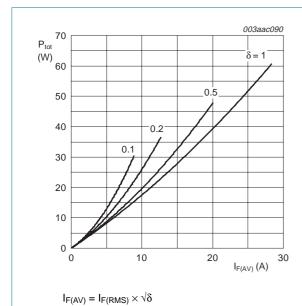
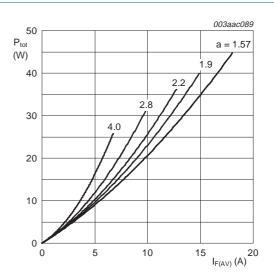


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

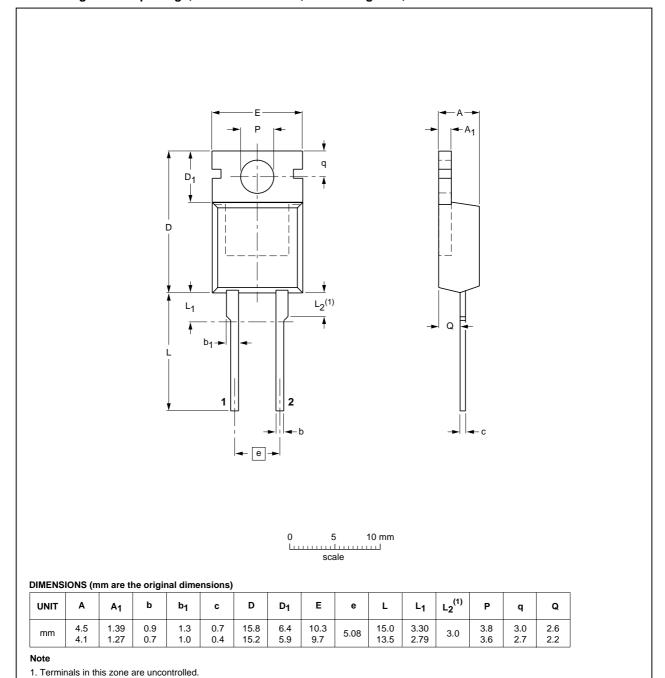


Fig 7. Package outline SOD59 (2-lead TO-220AC)

IEC

JEITA

REFERENCES

JEDEC

2-lead TO-220AC

OUTLINE

VERSION

SOD59

ISSUE DATE

99-09-13

EUROPEAN

PROJECTION

BYC20-600

Rectifier diode, hyperfast

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC20-600_1	20071128	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

BYC20-600

Rectifier diode, hyperfast

11. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 1
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 3
6	Characteristics 4
7	Package outline 7
8	Revision history 8
9	Legal information9
9.1	Data sheet status 9
9.2	Definitions
9.3	Disclaimers
9.4	Trademarks 9
10	Contact information 9
11	Contents

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